

42T03GP-VB Datasheet N-Channel 30-V (D-S) MOSFET

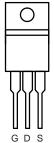
PRODUCT SUMMARY						
V _{DS} (V)	30					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0. 006					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0. 009					
I _D (A)	80					
Configuration	Single					
Package	TO-220AB					

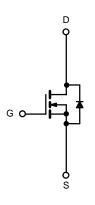
FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU









N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	.,,		
Gate-Source Voltage		V _{GS}	± 20	V	
	T _C = 25 °C		80		
Continuous Prain Current (T. – 175 °C)	T _C = 70 °C	L-	65		
Continuous Drain Current (T _J = 175 °C)	T _A = 25 °C	I _D	25.8 ^{b, c}		
	T _A = 70 °C		20 ^{b, c}	^	
Pulsed Drain Current	I _{DM}	200			
Avalanche Current Pulse	L = 0.1 mH	I _{AS}	39		
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	94.8	mJ	
Ocationary Course Brain Binds Comment	T _C = 25 °C	l-	50 ^{a, e}		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S —	3.13 ^{b, c}	A	
	T _C = 25 °C		120 ^a		
Maximum Power Dissipation	T _C = 70 °C	P _D	85	□ w	
	T _A = 25 °C	rD	3.75 ^{b, c}		
	T _A = 70 °C		2.63 ^{b, c}		
Operating Junction and Storage Temperature R	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Тур.	Max.	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	32	40	°C/W		
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6	- °C/W		

- Notes:
 a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.
 c. t = 10 sec.
 d. Maximum under steady state conditions is 90 °C/W.
 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		~\\/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	ι _D = 230 μΑ		- 7.5		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	1	V _{DS} = 30 V, V _{GS} = 0 V			1	μΑ
	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α
	Ъ	$V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		0.006		Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}$		0.009		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 28.8 \text{ A}$		160		S
Dynamic ^b						
Input Capacitance	C _{iss}			1600		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		525		pF
Reverse Transfer Capacitance	C _{rss}			370		
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		35	45	nC
				25	35	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 28.8 \text{ A}$		15		
Gate-Drain Charge	Q_{gd}			20		
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t _{d(on)}			18	27	ns
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.625 Ω		11	17	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 24$ A, V_{GEN} = 10 V, R_g = 1 Ω		70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}			55	83	
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.67 Ω		180	270	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 22.5$ A, V_{GEN} = 4.5 V, R_g = 1 Ω		55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristic	s					1
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			120	۸
Pulse Diode Forward Current ^a	I _{SM}				120	A
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 20 A di/dt 100 A/vo T 25 °C		70.2	105	nC
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		27		
Reverse Recovery Rise Time	t _b	7		25		ns

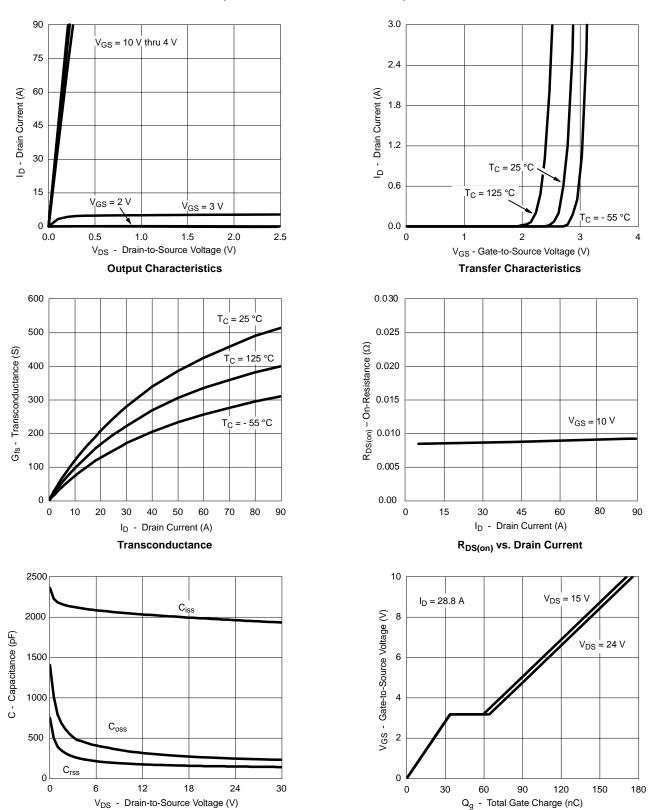
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



服务热线:400-655-8788

Capacitance

Gate Charge



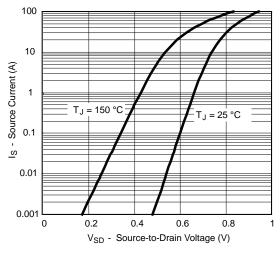
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



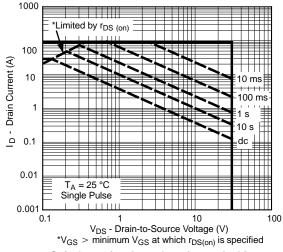
 $R_{DS(on)}\, vs.\, V_{GS}\, vs.\, Temperature$



Forward Diode Voltage vs. Temperature



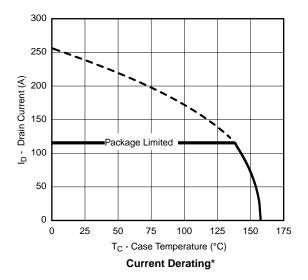
Threshold Voltage

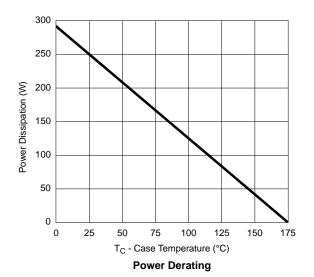


Safe Operating Area, Junction-to-Ambient

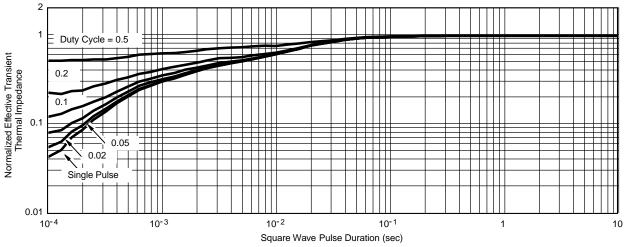


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





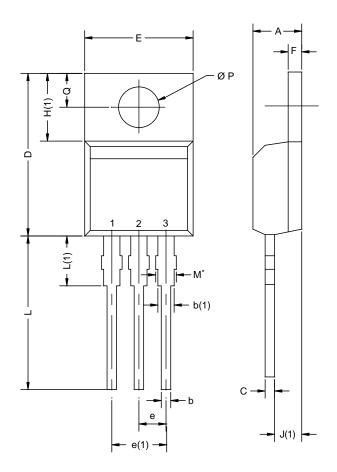
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case



TO-220AB



	MILLIM	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØР	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12					

DWG: 5471

Notes

 $^{^{\}star}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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